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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re application of: **Tomihide YASUMOTO**

Serial Number: **Not Yet Assigned**

Filed: **November 29, 2001**

For: **A SEMICONDUCTOR DEVICE MANUFACTURING METHOD USING
METAL SILICIDE REACTION AFTER ION IMPLANTATION IN
SILICON WIRING**

jc879 U.S. PTO
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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, D.C. 20231

November 29, 2001


Sir:

In compliance with 37 CFR 1.56, Applicant calls to the attention of the Patent and Trademark Office the reference listed on the attached PTO-1449.

A copy of the reference is enclosed herewith.

In the event there are any fees due in connection with the filing of this paper, please charge Deposit Account No. 01-2340.

Respectfully submitted,
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